

Yashwanth Balaji

List of Publications by Year in descending order

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Version: 2024-02-01

15
papers

497
citations

933264

10
h-index

1199470

12
g-index

15
all docs

15
docs citations

15
times ranked

980
citing authors

#	ARTICLE	IF	CITATIONS
1	MoS ₂ /MoTe ₂ Heterostructure Tunnel FETs Using Gated Schottky Contacts. <i>Advanced Functional Materials</i> , 2020, 30, 1905970.	7.8	50
2	Epitaxial registry and crystallinity of MoS ₂ via molecular beam and metalorganic vapor phase van der Waals epitaxy. <i>Applied Physics Letters</i> , 2020, 117, .	1.5	11
3	On the van der Waals Epitaxy of Homo-/Heterostructures of Transition Metal Dichalcogenides. <i>ACS Applied Materials & Interfaces</i> , 2020, 12, 27508-27517.	4.0	22
4	Fundamental limitation of van der Waals homoepitaxy by stacking fault formation in WSe ₂ . <i>2D Materials</i> , 2020, 7, 025027.	2.0	11
5	Devices and Circuits Using Novel 2-D Materials: A Perspective for Future VLSI Systems. <i>IEEE Transactions on Very Large Scale Integration (VLSI) Systems</i> , 2019, 27, 1486-1503.	2.1	30
6	Towards high-performance polarity-controllable FETs with 2D materials. , 2018, , .		4
7	Tunneling Transistors Based on MoS ₂ /MoTe ₂ Van der Waals Heterostructures. <i>IEEE Journal of the Electron Devices Society</i> , 2018, 6, 1048-1055.	1.2	33
8	Formation mechanism of 2D SnS ₂ and SnS by chemical vapor deposition using SnCl ₄ and H ₂ S. <i>Journal of Materials Chemistry C</i> , 2018, 6, 6172-6178.	2.7	56
9	Doping-Free Complementary Logic Gates Enabled by Two-Dimensional Polarity-Controllable Transistors. <i>ACS Nano</i> , 2018, 12, 7039-7047.	7.3	104
10	Doping-free complementary inverter enabled by 2D WSe ₂ electrostatically-doped reconfigurable transistors. , 2018, , .		0
11	Demonstration of $2 \times 10^{12} \text{ cm}^{-2}$ 2D-oxide interface trap density on back-gated MoS ₂ flake devices with 2.5 nm EOT. <i>Microelectronic Engineering</i> , 2017, 178, 145-149.	1.1	9
12	Tunneling transistors based on MoS ₂ /MoTe ₂ Van der Waals heterostructures. , 2017, , .		2
13	Controlled Sulfurization Process for the Synthesis of Large Area MoS ₂ Films and MoS ₂ /WS ₂ Heterostructures. <i>Advanced Materials Interfaces</i> , 2016, 3, 1500635.	1.9	61
14	Molecular doping of MoS ₂ transistors by self-assembled oleylamine networks. <i>Applied Physics Letters</i> , 2016, 109, .	1.5	41
15	Polarity control in WSe ₂ double-gate transistors. <i>Scientific Reports</i> , 2016, 6, 29448.	1.6	63